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## FDG330P

## P－Channel 1．8V Specified PowerTrench ${ }^{\circledR}$ MOSFET

## General Description

This P－Channel 1.8 V specified MOSFET uses Fairchild＇s advanced low voltage PowerTrench process． It has been optimized for battery power management applications．

## Applications

－Battery management
－Load switch

## Features

－$-2 \mathrm{~A},-12 \mathrm{~V} . \quad \mathrm{R}_{\mathrm{DS}(\mathrm{ON})}=110 \mathrm{~m} \Omega @ \mathrm{~V}_{G S}=-4.5 \mathrm{~V}$
$R_{\mathrm{DS}(\mathrm{ON})}=150 \mathrm{~m} \Omega$＠ $\mathrm{V}_{\mathrm{GS}}=-2.5 \mathrm{~V}$
$\mathrm{R}_{\mathrm{DS}(\mathrm{ON})}=215 \mathrm{~m} \Omega @ \mathrm{~V}_{\mathrm{GS}}=-1.8 \mathrm{~V}$
－Low gate charge
－High performance trench technology for extremely low $\mathrm{R}_{\mathrm{DS}(\mathrm{ON})}$
－Compact industry standard SC70－6 surface mount package


SC70－6


Absolute Maximum Ratings $T_{A}=2^{\circ} \mathrm{C}$ unless otherwise noted

| Symbol | Parameter |  | Ratings | Units |
| :---: | :---: | :---: | :---: | :---: |
| V ${ }_{\text {DSs }}$ | Drain－Source Voltage |  | －12 | V |
| $\mathrm{V}_{\text {GSS }}$ | Gate－Source Voltage |  | $\pm 8$ | V |
| $\mathrm{I}_{\mathrm{D}}$ | Drain Current - Continuous <br>  - Pulsed | （Note 1a） | －2 | A |
|  |  |  | －6 |  |
| $\mathrm{P}_{\mathrm{D}}$ | Power Dissipation for Single Operation | （Note 1a） （Note 1b） | 0.75 | W |
|  |  |  | 0.48 |  |
| $\mathrm{T}_{\mathrm{J},} \mathrm{T}_{\text {STG }}$ | Operating and Storage Junction Temperature Range |  | －55 to＋150 | ${ }^{\circ} \mathrm{C}$ |

Thermal Characteristics

| $\mathrm{R}_{\theta \mathrm{JA}}$ | Thermal Resistance，Junction－to－Ambient | Note 1b） | 260 | ${ }^{\circ} \mathrm{C} / \mathrm{W}$ |
| :--- | :--- | :--- | :--- | :--- |

## Package Marking and Ordering Information

| Device Marking | Device | Reel Size | Tape width | Quantity |
| :---: | :---: | :---: | :---: | :---: |
| .30 | FDG330P | $7^{\prime \prime}$ | 8 mm | 3000 units |


| Electrical Characteristics |  | $\mathrm{T}_{\mathrm{A}}=25^{\circ} \mathrm{C}$ unless otherwise noted |  |  |  |  |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| Symbol | Parameter | Test Conditions | Min | Typ | Max | Units |
| Off Characteristics |  |  |  |  |  |  |
| BV ${ }_{\text {DSS }}$ | Drain-Source Breakdown Voltage | $\mathrm{V}_{G S}=0 \mathrm{~V}, \quad \mathrm{I}_{\mathrm{D}}=-250 \mu \mathrm{~A}$ | -12 |  |  | V |
| $\frac{\Delta \mathrm{BV}_{\mathrm{DSS}}}{\Delta \mathrm{~T}_{\mathrm{J}}}$ | Breakdown Voltage Temperature Coefficient | $\mathrm{I}_{\mathrm{D}}=-250 \mu \mathrm{~A}$, Referenced to $25^{\circ} \mathrm{C}$ |  | -2.7 |  | $\mathrm{mV} /{ }^{\circ} \mathrm{C}$ |
| IDSS | Zero Gate Voltage Drain Current | $\mathrm{V}_{\mathrm{DS}}=-10 \mathrm{~V}, \mathrm{~V}_{\mathrm{GS}}=0 \mathrm{~V}$ |  |  | -1 | $\mu \mathrm{A}$ |
| IGSSF | Gate-Body Leakage, Forward | $\mathrm{V}_{\mathrm{GS}}=8 \mathrm{~V}, \quad \mathrm{~V}_{\mathrm{DS}}=0 \mathrm{~V}$ |  |  | 100 | nA |
| IGSSR | Gate-Body Leakage, Reverse | $\mathrm{V}_{G S}=-8 \mathrm{~V}, \quad \mathrm{~V}_{\mathrm{DS}}=0 \mathrm{~V}$ |  |  | -100 | nA |
| On Characteristics (Note 2) |  |  |  |  |  |  |
| $\mathrm{V}_{\mathrm{GS}(\mathrm{th})}$ | Gate Threshold Voltage | $\mathrm{V}_{\mathrm{DS}}=\mathrm{V}_{\mathrm{GS}}, \quad \mathrm{I}_{\mathrm{D}}=-250 \mu \mathrm{~A}$ | -0.4 | -0.7 | -1.5 | V |
| $\begin{gathered} \hline \Delta \mathrm{V}_{\mathrm{GS}(\mathrm{th})} \\ \Delta \mathrm{T}_{\mathrm{J}} \end{gathered}$ | Gate Threshold Voltage Temperature Coefficient | $\mathrm{I}_{\mathrm{D}}=-250 \mu \mathrm{~A}$, Referenced to $25^{\circ} \mathrm{C}$ |  | 2.3 |  | $\mathrm{mV} /{ }^{\circ} \mathrm{C}$ |
| $\mathrm{R}_{\mathrm{DS} \text { (on) }}$ | Static Drain-Source On-Resistance | $\begin{aligned} & \mathrm{V}_{\mathrm{GS}}=-4.5 \mathrm{~V}, \quad \mathrm{I}_{\mathrm{D}}=-2.0 \mathrm{~A} \\ & \mathrm{~V}_{\mathrm{GS}}=-2.5 \mathrm{~V}, \quad \mathrm{I}_{\mathrm{D}}=-1.7 \mathrm{~A} \\ & \mathrm{~V}_{\mathrm{GS}}=-1.8 \mathrm{~V}, \quad \mathrm{I}_{\mathrm{D}}=-1.4 \mathrm{~A} \\ & \mathrm{~V}_{\mathrm{GS}}=-4.5 \mathrm{~V}, \mathrm{I}_{\mathrm{D}}=-2.0 \mathrm{~A}, \mathrm{~T}_{\mathrm{J}}=125^{\circ} \mathrm{C} \end{aligned}$ |  | $\begin{gathered} \hline 84 \\ 107 \\ 145 \\ 98 \end{gathered}$ | $\begin{aligned} & 110 \\ & 150 \\ & 215 \\ & 148 \end{aligned}$ | $\mathrm{m} \Omega$ |
| $\mathrm{I}_{\mathrm{D} \text { (on) }}$ | On-State Drain Current | $\mathrm{V}_{\mathrm{GS}}=-4.5 \mathrm{~V}, \mathrm{~V}_{\mathrm{DS}}=-5 \mathrm{~V}$ | -6 |  |  | A |
| $\mathrm{g}_{\text {FS }}$ | Forward Transconductance | $\mathrm{V}_{\mathrm{DS}}=-5 \mathrm{~V}, \quad \mathrm{I}_{\mathrm{D}}=-2.0 \mathrm{~A}$ |  | 6.8 |  | S |
| Dynamic Characteristics |  |  |  |  |  |  |
| $\mathrm{C}_{\text {iss }}$ | Input Capacitance | $\mathrm{V}_{\mathrm{DS}}=-6.0 \mathrm{~V}, \quad \mathrm{~V}_{\mathrm{GS}}=0 \mathrm{~V}$, |  | 477 |  | pF |
| $\mathrm{C}_{\text {oss }}$ | Output Capacitance | $\mathrm{f}=1.0 \mathrm{MHz}$ |  | 186 |  | pF |
| $\mathrm{C}_{\text {rss }}$ | Reverse Transfer Capacitance |  |  | 124 |  | pF |
| Switching Characteristics (Note 2) |  |  |  |  |  |  |
| $\mathrm{t}_{\mathrm{d} \text { (on) }}$ | Turn-On Delay Time | $\mathrm{V}_{\mathrm{DD}}=-6.0 \mathrm{~V}, \quad \mathrm{I}_{\mathrm{D}}=1 \mathrm{~A},$ |  | 10 | 20 | ns |
| $\mathrm{t}_{\mathrm{r}}$ | Turn-On Rise Time | $V_{G S}=-4.5 \mathrm{~V}, \mathrm{R}_{\mathrm{GEN}}=6 \Omega$ |  | 11 | 20 | ns |
| $\mathrm{t}_{\mathrm{d} \text { (off) }}$ | Turn-Off Delay Time |  |  | 12 | 22 | ns |
| $\mathrm{t}_{\mathrm{f}}$ | Turn-Off Fall Time |  |  | 18 | 32 | ns |
| $\mathrm{Q}_{\mathrm{g}}$ | Total Gate Charge | $\mathrm{V}_{\mathrm{DS}}=-6.0 \mathrm{~V}, \quad \mathrm{I}_{\mathrm{D}}=-2.0 \mathrm{~A},$ |  | 5 | 7 | nC |
| $\mathrm{Q}_{\mathrm{gs}}$ | Gate-Source Charge | $\mathrm{V}_{G S}=-4.5 \mathrm{~V}$ |  | 0.8 |  | nC |
| $\mathrm{Q}_{\mathrm{gd}}$ | Gate-Drain Charge |  |  | 1.4 |  | nC |
| Drain-Source Diode Characteristics and Maximum Ratings |  |  |  |  |  |  |
| $\mathrm{I}_{\text {S }}$ | Maximum Continuous Drain-Sourc | Diode Forward Current |  |  | -0.62 | A |
| $\mathrm{V}_{\text {SD }}$ | Drain-Source Diode Forward Voltage | $\mathrm{V}_{\mathrm{GS}}=0 \mathrm{~V}, \quad \mathrm{I}$ S $=-0.62 \mathrm{~A}$ (Note 2) |  | -0.7 | -1.2 | V |
| 1. $R_{\theta J A}$ is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. $R_{\theta J C}$ is guaranteed by design while $R_{\theta C A}$ is determined by the user's board design. <br> a.) $170^{\circ} \mathrm{C} / \mathrm{W}$ when mounted on a $1 \mathrm{in}^{2}$ pad of 2 oz . copper. <br> b.) $260^{\circ} \mathrm{C} / \mathrm{W}$ when mounted on a minimum pad. <br> 2. Pulse Test: Pulse Width < 300 $\mu \mathrm{s}$, Duty Cycle $<2.0 \%$ |  |  |  |  |  |  |

## Typical Characteristics



Figure 1. On-Region Characteristics.


Figure 3. On-Resistance Variation with Temperature.


Figure 5. Transfer Characteristics.


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

## Typical Characteristics <br> 

Figure 7. Gate Charge Characteristics.


Figure 9. Maximum Safe Operating Area.


Figure 8. Capacitance Characteristics.


Figure 10. Single Pulse Maximum Power Dissipation.


Figure 11. Transient Thermal Response Curve.
Thermal characterization performed using the conditions described in Note 1b. Transient thermal response will change depending on the circuit board design.

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